

SKM 75GB123D



SEMITRANS[®] 2

IGBT Modules

SKM 75GB123D

SKM 75GAL123D

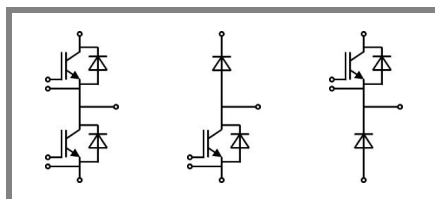
SKM 75GAR123D

Features

- MOS input (voltage controlled)
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to $6 \times I_{Cnom}$
- Latch-up free
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology
- Large clearance (10 mm) and creepage distance (20 mm)

Typical Applications*

- AC inverter drives
- UPS



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GAL

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Absolute Maximum Ratings		$T_c = 25\text{ }^\circ\text{C}$, unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}	$T_j = 25\text{ }^\circ\text{C}$	1200		V
I_C	$T_j = 150\text{ }^\circ\text{C}$	$T_{case} = 25\text{ }^\circ\text{C}$	75	A
		$T_{case} = 80\text{ }^\circ\text{C}$	60	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	150		A
V_{GES}		± 20		V
t_{psc}	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125\text{ }^\circ\text{C}$ $V_{CES} < 1200\text{ V}$	10		μs
Inverse Diode				
I_F	$T_j = 150\text{ }^\circ\text{C}$	$T_{case} = 25\text{ }^\circ\text{C}$	75	A
		$T_{case} = 80\text{ }^\circ\text{C}$	50	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	150		A
I_{FSM}	$t_p = 10\text{ ms}; \sin.$	$T_j = 150\text{ }^\circ\text{C}$	480	
Freewheeling Diode				
I_F	$T_j = 150\text{ }^\circ\text{C}$	$T_{case} = 25\text{ }^\circ\text{C}$	95	A
		$T_{case} = 80\text{ }^\circ\text{C}$	65	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	200		A
I_{FSM}	$t_p = 10\text{ ms}; \sin$	$T_j = 150\text{ }^\circ\text{C}$	720	
Module				
$I_{t(RMS)}$		200		A
T_{vj}		- 40 ... + 150		$^\circ\text{C}$
T_{stg}		- 40 ... + 125		$^\circ\text{C}$
V_{isol}	AC, 1 min.	2500		V

Characteristics		$T_c = 25\text{ }^\circ\text{C}$, unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units	
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 2\text{ mA}$	4,5	5,5	6,5	V	
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25\text{ }^\circ\text{C}$		0,1	0,3	
V_{CE0}		$T_j = 25\text{ }^\circ\text{C}$		1,4	1,6	
		$T_j = 125\text{ }^\circ\text{C}$		1,6	1,8	
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ }^\circ\text{C}$		22	28	
		$T_j = 125\text{ }^\circ\text{C}$		30	38	
$V_{CE(sat)}$	$I_{Cnom} = 50\text{ A}, V_{GE} = 15\text{ V}$	$T_j = \text{ }^\circ\text{C}_{chiplev.}$		2,5	3	
C_{ies}	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$		3,3	4,3	
C_{oes}				0,5	0,6	
C_{res}				0,22	0,3	
Q_G	$V_{GE} = -8 - +20\text{ V}$			500	nC	
R_{Gint}	$T_j = \text{ }^\circ\text{C}$			5	Ω	
$t_{d(on)}$	$R_{Gon} = 22\text{ }^\circ\Omega$	$V_{CC} = 600\text{ V}$ $I_C = 50\text{ A}$			44	100
t_r					56	100
E_{on}					8	
$t_{d(off)}$	$R_{Goff} = 22\text{ }^\circ\Omega$	$T_j = 125\text{ }^\circ\text{C}$ $V_{GE} = \pm 15\text{ V}$			380	500
t_f					70	100
E_{off}					5	
$R_{th(j-c)}$	per IGBT			0,27	K/W	

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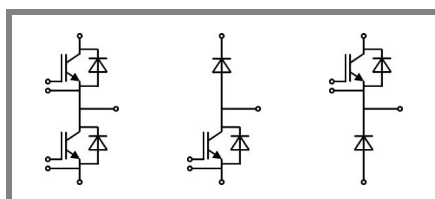
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Characteristics		min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 50 \text{ A}; V_{GE} = 0 \text{ V}$		2	2,5	V
			1,8		V
V_{F0}			1,1	1,2	V
					V
r_F			18	26	mΩ
					mΩ
I_{RRM}	$I_F = 50 \text{ A}$		35		A
Q_{rr}	$di/dt = 800 \text{ A}/\mu\text{s}$				μC
E_{rr}	$V_{GE} = 0 \text{ V}; V_{CC} = 600 \text{ V}$				mJ
$R_{th(j-c)D}$	per diode			0,6	K/W
Freewheeling Diode					
$V_F = V_{EC}$	$I_{Fnom} = 50 \text{ A}; V_{GE} = 0 \text{ V}$		1,85	2,2	V
			1,6		V
V_{F0}			1,1	1,2	V
					V
r_F			15	20	V
					V
I_{RRM}	$I_F = 50 \text{ A}$		40		A
Q_{rr}					μC
E_{rr}	$V_{GE} = 0 \text{ V}; V_{CC} = 600 \text{ V}$				mJ
$R_{th(j-c)FD}$	per diode			0,5	K/W
Module					
L_{CE}				30	nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25 \text{ °C}$	0,75		mΩ
		$T_{case} = 125 \text{ °C}$	1		mΩ
$R_{th(c-s)}$	per module			0,05	K/W
M_s	to heat sink M6		3	5	Nm
M_t	to terminals M5		2,5	5	Nm
w				160	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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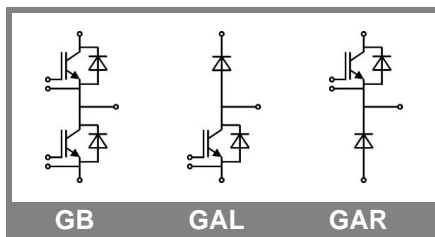
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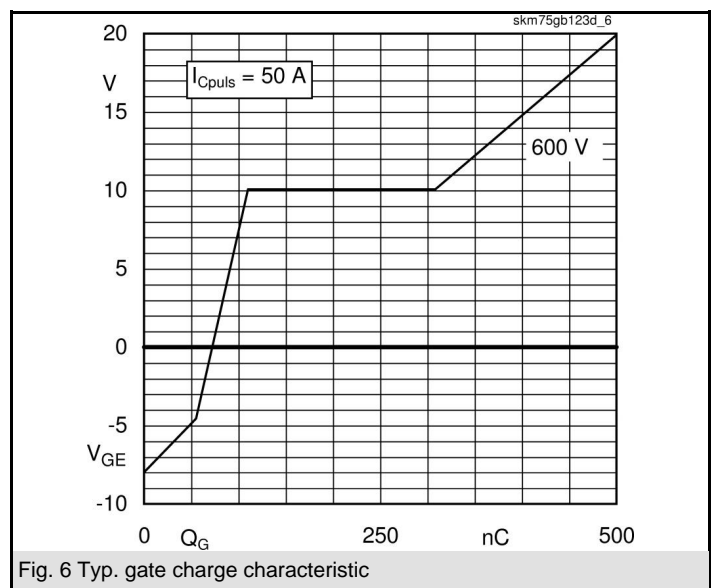
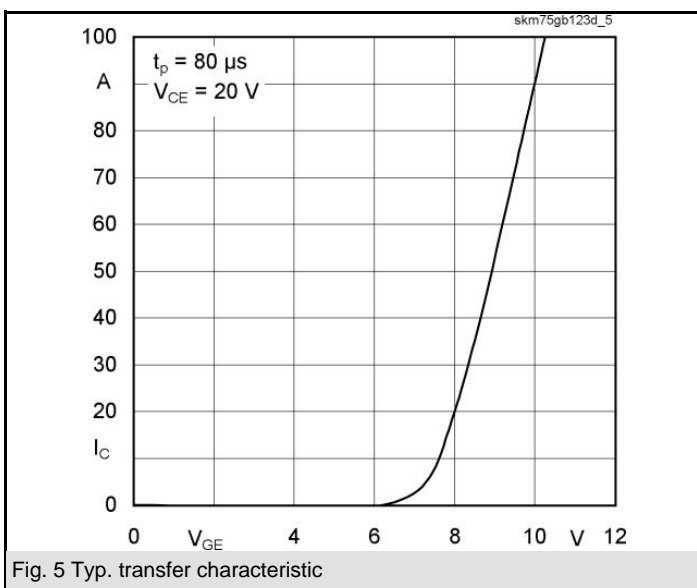
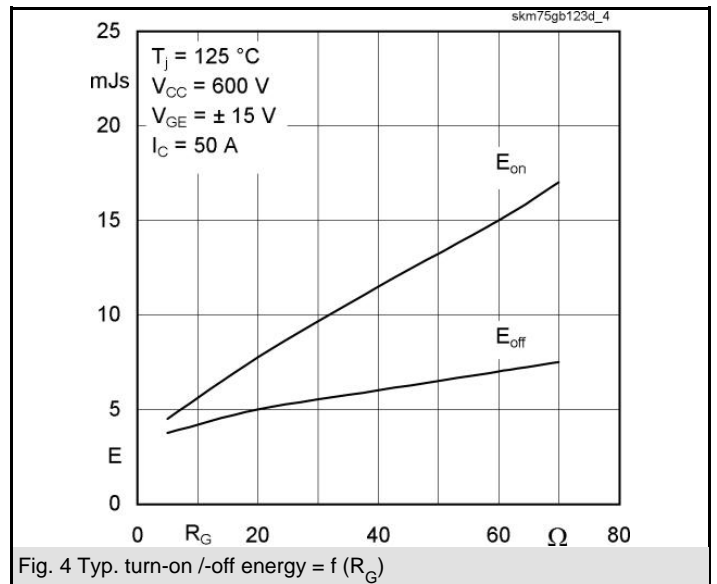
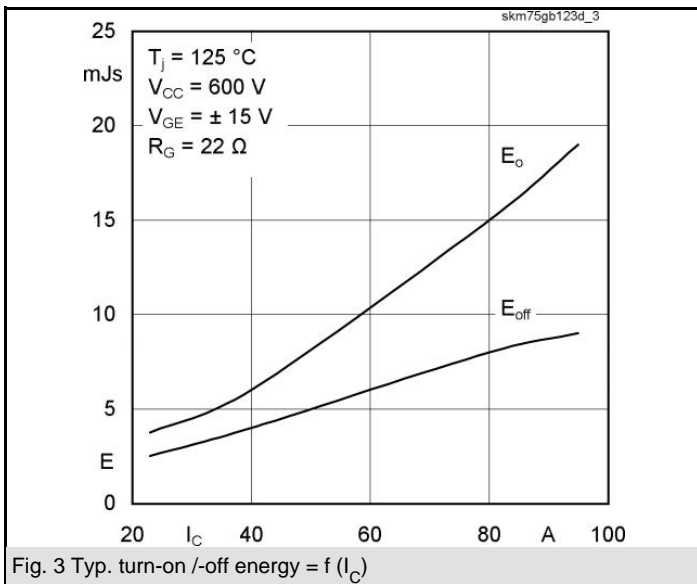
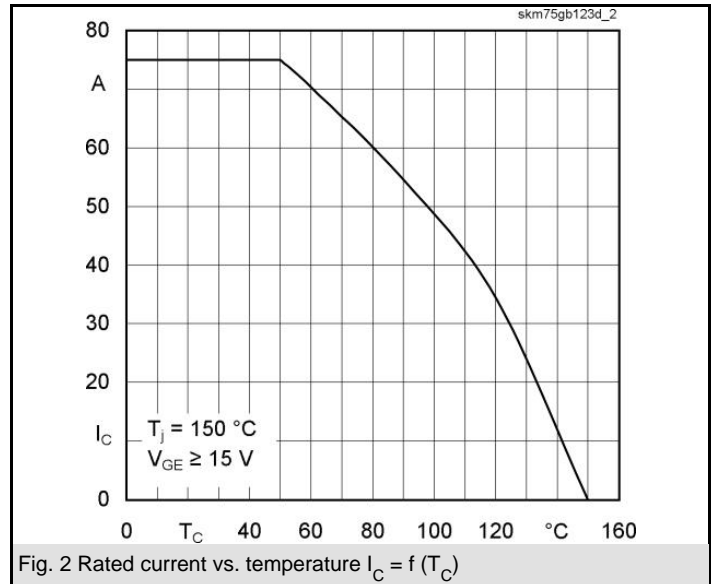
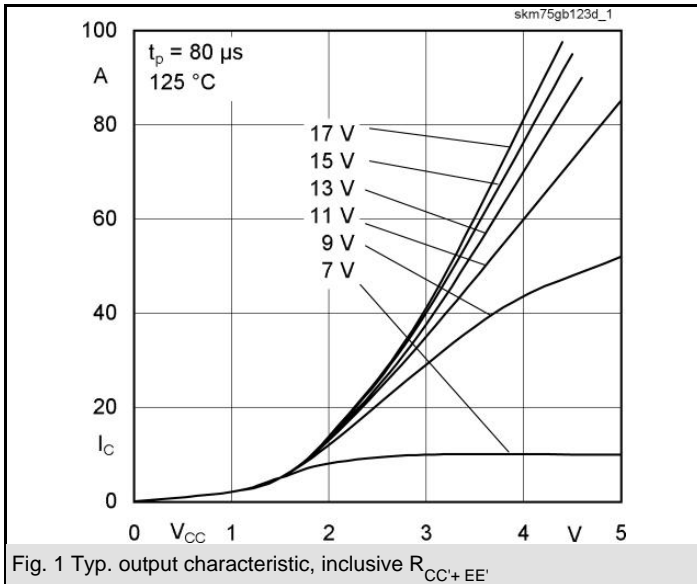
Z_{th}		Conditions	Values	Units
$Z_{th(j-c)I}$				
$R_{\theta j-c}$	$i = 1$		180	mk/W
$R_{\theta j-c}$	$i = 2$		64	mk/W
$R_{\theta j-c}$	$i = 3$		22	mk/W
$R_{\theta j-c}$	$i = 4$		4	mk/W
$\tau_{\theta j-c}$	$i = 1$		0,0327	s
$\tau_{\theta j-c}$	$i = 2$		0,0479	s
$\tau_{\theta j-c}$	$i = 3$		0,008	s
$\tau_{\theta j-c}$	$i = 4$		0,005	s
$Z_{th(j-c)D}$				
$R_{\theta j-cD}$	$i = 1$		380	mk/W
$R_{\theta j-cD}$	$i = 2$		190	mk/W
$R_{\theta j-cD}$	$i = 3$		26	mk/W
$R_{\theta j-cD}$	$i = 4$		4	mk/W
$\tau_{\theta j-cD}$	$i = 1$		0,0947	s
$\tau_{\theta j-cD}$	$i = 2$		0,006	s
$\tau_{\theta j-cD}$	$i = 3$		0,08	s
$\tau_{\theta j-cD}$	$i = 4$		0,003	s

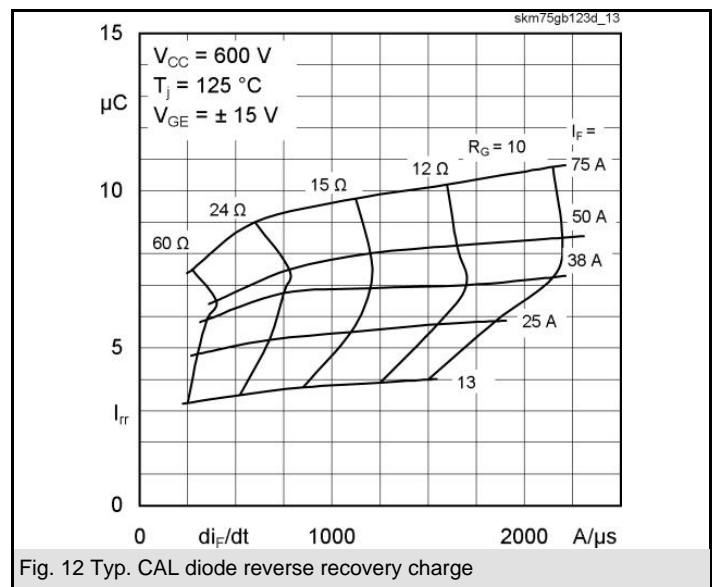
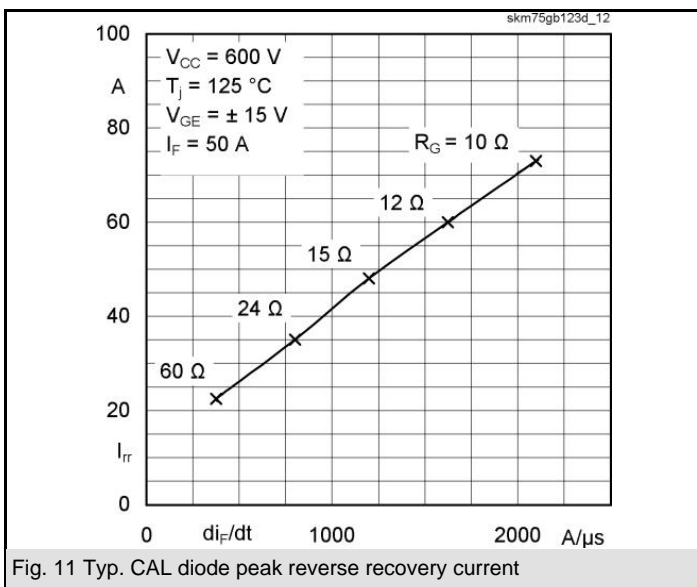
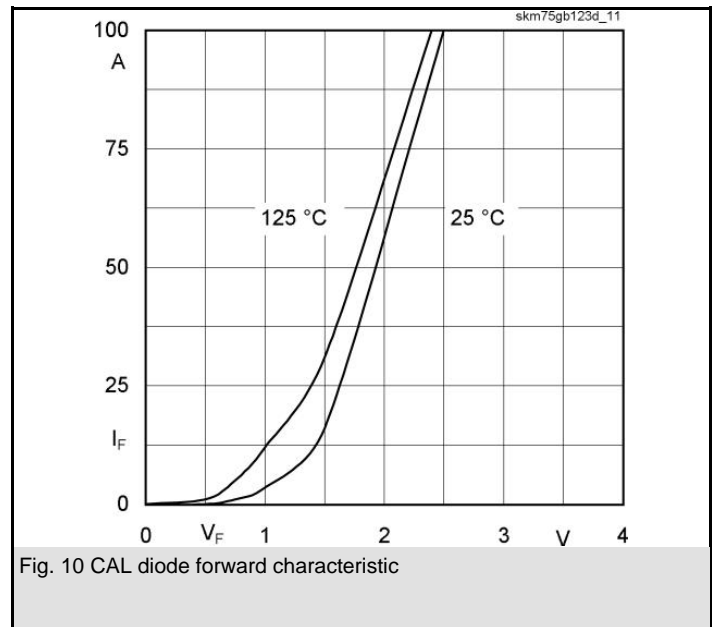
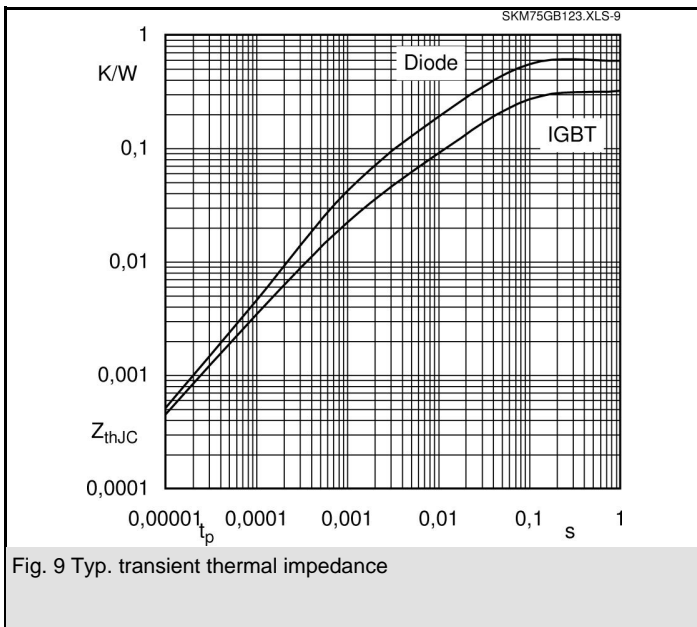
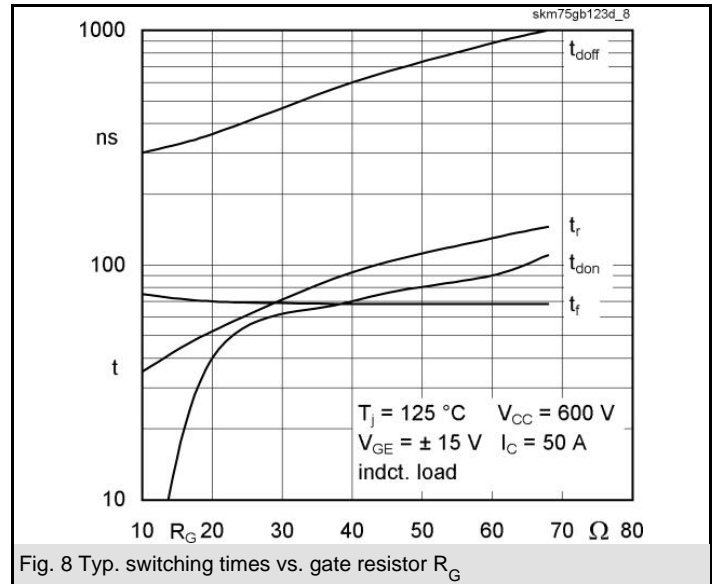
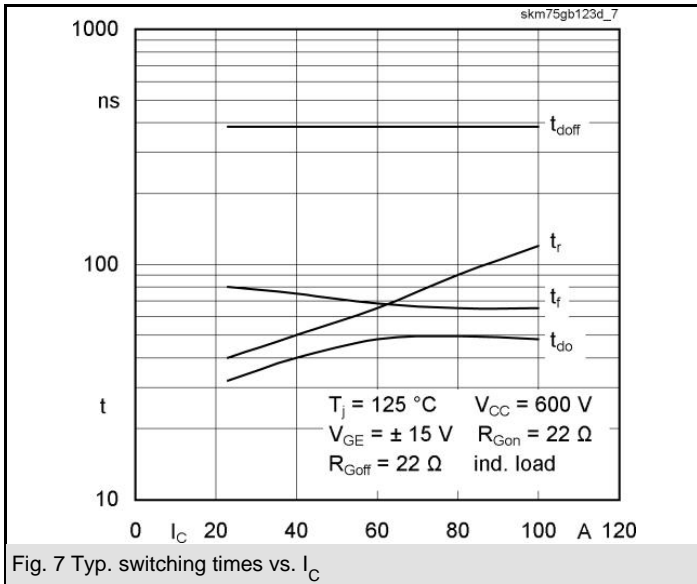


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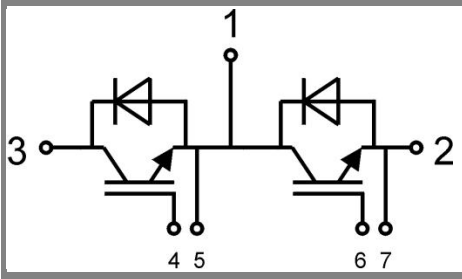
UL Recognized

CASED61

File 63 532



Case D 61



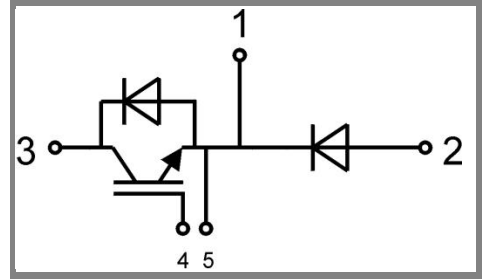
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Case D 61



GAL

Case D 62 (→ D 61)



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Case D 63 (→ D 61)